

<b>Module Code</b>	<b>EEU44C02</b>
<b>Module Name</b>	Microelectronic Circuits
<b>ECTS Weighting<sup>2</sup></b>	5 ECTS
<b>Semester taught</b>	Semester 2
<b>Module Coordinator/s</b>	Dr Justin King
<b><u>Module Learning Outcomes</u> with reference to the <u>Graduate Attributes</u> and how they are developed in discipline</b>	<p>On successful completion of this module, students should be able to:</p> <p>LO 1: Explain the electrical operation of the metal-oxide-semiconductor (MOS) field effect transistor.</p> <p>LO 2: Analyse the fundamental static and dynamic performance of simple CMOS circuits noting design trade-offs.</p> <p>LO 3: Implement various CMOS logic structures.</p> <p>LO 4: Determine the limitations of current CMOS structures and alternatives.</p> <p>LO 5: Extend knowledge of dynamic performance to more complex logic structures and systems.</p> <p>LO 6: Demonstrate the fundamental principles of system design.</p> <p><b>Graduate Attributes: levels of attainment</b></p> <p>To act responsibly - Enhanced</p> <p>To think independently - Enhanced</p> <p>To develop continuously - Enhanced</p> <p>To communicate effectively - Enhanced</p>

<sup>1</sup> [An Introduction to Module Design](#) from AISHE provides a great deal of information on designing and re-designing modules.

<sup>2</sup> [TEP Glossary](#)

**Module Content**

Please provide a brief overview of the module of no more than 350 words written so that someone outside of your discipline will understand it.

- **The MOSFET:** Physical principles of device operation; current voltage relationships, device models; second order effects.
- **Static Circuit Analysis:** MOS inverters; the CMOS inverter transfer characteristic and its switching level; NAND and NOR gates; noise margin; transmission gate.
- **Dynamic Circuit Analysis:** Circuit lay-out, MOS transistor capacitances; inverter step response; gate delays; power dissipation.
- **Technology Scaling, 14 Nanometers and Beyond:** Limitations and emerging technologies. FinFETs.
- **CMOS Logic Functions:** Generalised CMOS combinational logic; XOR and transmission gate logic; sequential logic elements, SRAM, DRAM.
- **CMOS Subsystem Performance:** RC gate delay models.

**Teaching and Learning Methods**

e.g., lectures, seminars, online learning via VLE, field trips, laboratories, practice-based etc...

This module is taught using a combination of lectures, tutorials and two supporting laboratories. During the tutorials, students will develop their problem solving skills by tackling problems based on the lecture material.

**Assessment Details<sup>3</sup>**

Please include the following:

- Assessment Component
- Assessment description
- Learning Outcome(s) addressed
- % of total
- Assessment due date

Assessment Component	Assessment Description	LO Addressed	% of total	Week due
Written Exam	Written Exam		80	End of Semester
Laboratory	Laboratory		20	During Semester

**Reassessment Requirements**

Supplemental Written Exam

**Contact Hours and Indicative Student Workload<sup>3</sup>**

**Contact hours:**  
36 hours

<sup>3</sup> [TEP Guidelines on Workload and Assessment](#)

	<p><b>Independent Study (preparation for course and review of materials):</b> 35</p> <hr/> <p><b>Independent Study (preparation for assessment, incl. completion of assessment):</b> 40</p>
<b>Recommended Reading List</b>	<p>CMOS Digital Integrated Circuits: Analysis and Design, SM Kang and Y Leblebici, McGraw-Hill, 1996.</p> <p>CMOS VLSI Design: a circuits and systems perspective, 4th ed., Neil Weste and David Harris, Pearson Addison Wesley, 2011.</p> <p>Device Electronics for Integrated Circuits, Richard Muller and Theodore Kamins, John Wiley, 2003.</p>
<b>Module Pre-requisite</b>	EEU33C03 or equivalent
<b>Module Co-requisite</b>	
<b>Module Website</b>	See Blackboard
<b>Are other Schools/Departments involved in the delivery of this module? If yes, please provide details.</b>	No
<b>Module Approval Date</b>	
<b>Approved by</b>	
<b>Academic Start Year</b>	2020
<b>Academic Year of Date</b>	2019/2020